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IN THE CLAIMS:

1. (Previously Presented) A method for forming a porous dielectric film, comprising:
forming a silicon based film having a water soluble compound dispersed therein, wherein the water soluble compound is boron oxide provided by an organoboron compound introduced while forming the silicon based film; and
removing at least a portion of the water soluble compound, thereby providing the porous dielectric film.

2-4. (Cancelled)

5. (Original) The method of claim 1, wherein the forming the silicon based film is by chemical vapor deposition (CVD).

6. (Cancelled)

7. (Original) The method of claim 1, wherein the silicon based film is a carbon doped silicon based film.

8. (Original) The method of claim 1, wherein the removing the at least a portion of the water soluble compound is by wet etching the silicon based film.

9. (Original) The method of claim 1, further comprising treating the porous dielectric film with an electron beam.

10. (Original) The method of claim 1, wherein the dielectric constant of the porous dielectric film is less than 2.0.

11. (Original) The method of claim 1, wherein the porosity of the porous dielectric film is at least forty percent.

12-16. (Cancelled)

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17. (Currently Amended) A method for forming a porous dielectric film, comprising:
doping of controlled size nano phase ~~compounds~~ compound in a silicon based
film using chemical vapor deposition (CVD), wherein the nano phase ~~compounds~~ compound are
compound is boron oxide (B_2O_3); and
removing at least a portion of the nano phase ~~compounds~~ compound dispersed
in the silicon based film, thereby providing the porous dielectric film.
18. (Original) The method of claim 17, wherein the silicon based film is a carbon
doped silicon based film.
19. (Original) The method of claim 17, wherein the nano phase compounds are
soluble in water.
20. (Original) The method of claim 17, further comprising treating the porous
dielectric film with an electron beam.

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